



DMTH10H017LPD

100V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
100V	17.4mΩ @ V _{GS} = 10V	59A
	$30.3 \text{m}\Omega @ V_{\text{GS}} = 4.5 \text{V}$	45A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

- Synchronous Rectifier
- DC-DC Converters
- Primary Side Switching

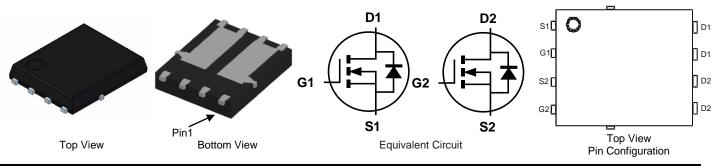
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH10H017LPDQ)

Mechanical Data

• Case: PowerDl[®]5060-8

- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

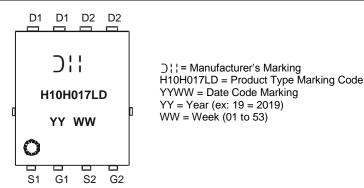
Part Number	Case	Packaging
DMTH10H017LPD-13	PowerDI5060-8 (Type E)	2500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		۱ _D	59 42	А
Maximum Body Diode Forward Current (Note 6)	ls	60	А	
Pulsed Drain Current (10µs Pulse, T _C = +25°C, Package Limited)	I _{DM}	236	A	
Pulsed Body Diode Forward Current (10µs Pulse, T _C = +25°C, Package Lin	I _{SM}	236	А	
Avalanche Current, L = 3mH (Note 9)	I _{AS}	10	A	
Avalanche Energy, L = 3mH (Note 9)	E _{AS}	150	mJ	
Avalanche Current, L = 1mH (Note 9)		I _{AS}	10	A
Avalanche Energy, L = 1mH (Note 9)	E _{AS}	50	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	56	°C/W
Total Power Dissipation	$T_{\rm C} = +25^{\circ}{\rm C}$	PD	93	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1.6	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol	IVIIII	тур	WIGA	Unit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	100			V	$V_{GS} = 0V, I_D = 1mA$	
5							
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)				1		-	
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	13.7	17.4	mΩ	$V_{GS} = 10V, I_D = 17A$	
	NDS(ON)	_	23.8	30.3	11152	$V_{GS} = 4.5V, I_D = 10A$	
Diode Forward Voltage	V _{SD}	_	_	1.3	V	$V_{GS} = 0V, I_{S} = 17A$	
DYNAMIC CHARACTERISTICS (Note 8)					•	÷	
Input Capacitance	C _{iss}	_	1986	—	pF	$V_{DS} = 50V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	333	—			
Reverse Transfer Capacitance	C _{rss}	_	20	_			
Gate Resistance	R _G		1.17	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	14.4	—			
Total Gate Charge (V _{GS} = 10V)	Qg	_	28.6	—	nC	$V_{DS} = 50V, I_D = 20A$	
Gate-Source Charge	Q _{gs}	_	5.2	—			
Gate-Drain Charge	Q _{gd}	_	8.2	—			
Turn-On Delay Time	t _{D(ON)}		9.8	_		$V_{DD} = 50V, V_{GS} = 10V,$ $R_G = 11\Omega, I_D = 20A$	
Turn-On Rise Time	t _R	_	16.3	_	1		
Turn-Off Delay Time	t _{D(OFF)}		32.6		ns		
Turn-Off Fall Time	t _F		21.6]		
Body Diode Reverse Recovery Time	t _{RR}	_	40.6	_	ns	I _F = 17A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	58.1	_	nC	I _F = 17A, di/dt = 100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Thermal resistance from junction to solder point (on the exposed drain pin).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:

9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.



DMTH10H017LPD

T_J = 85℃

4.5

5

T_J = 25℃

T_I = -55℃

4

12

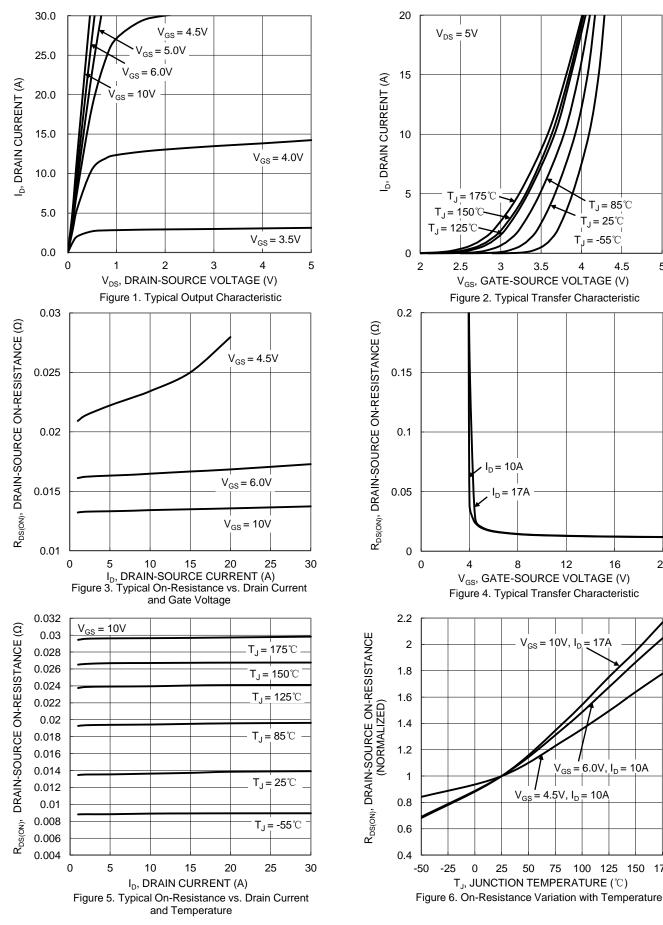
16

174

 $V_{GS} = 6.0V, I_{D} = 10A$

75 100 125 150 175

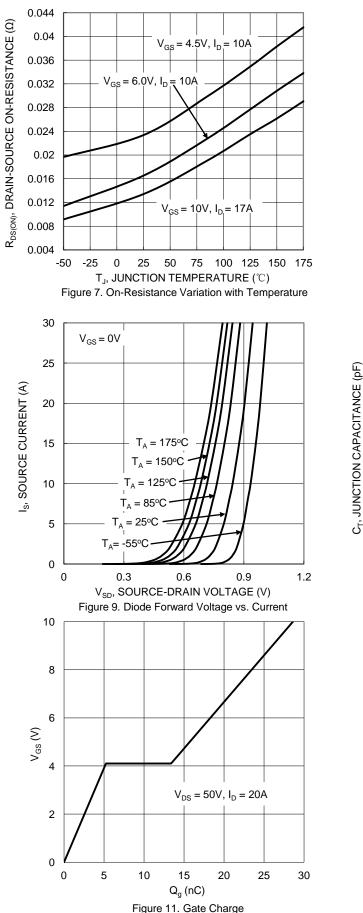
20



DMTH10H017LPD Document number: DS40752 Rev. 4 - 2



DMTH10H017LPD



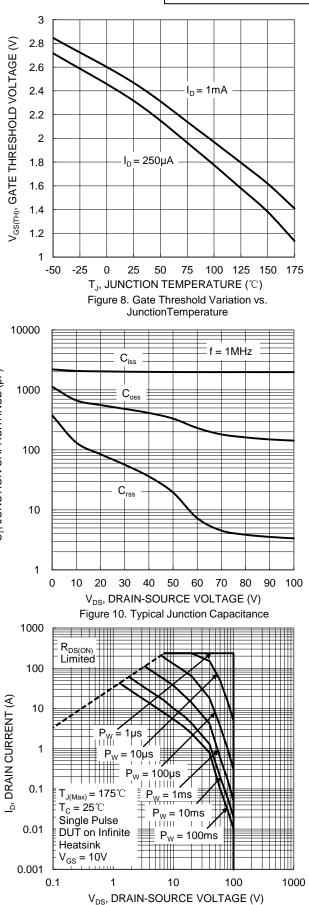
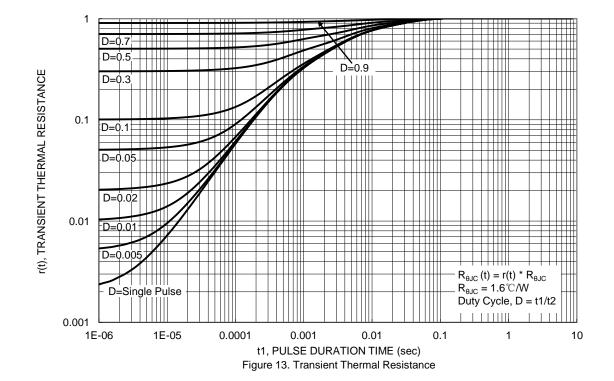


Figure 12. SOA, Safe Operation Area

DMTH10H017LPD Document number: DS40752 Rev. 4 - 2





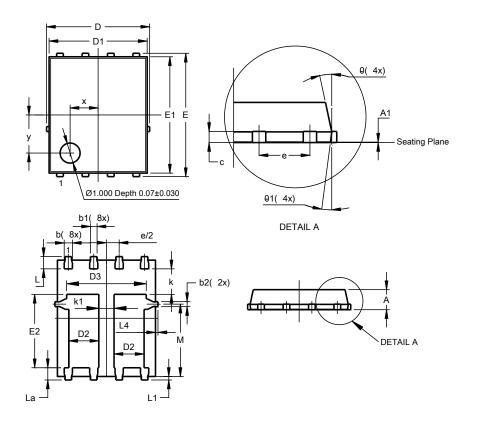




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type E)

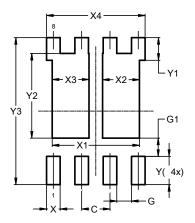


	PowerDI5060-8 (Type E)					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
С	0.23	0.33	0.277			
D	5	.15 BS(0			
D1	4.85	4.95	4.90			
D2	1.40	1.60	1.50			
D3	-	- 3.98				
Е	6	.15 BS(0			
E1	5.75	5.85	5.80			
E2	3.56	3.76	3.66			
е	1	.27BSC				
k	-	-	1.27			
k1	0.56	-	-			
L	0.51	0.71	0.61			
La	0.51	0.71	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
М	3.50	3.71	3.605			
х	-	- 1.40				
у	-	-	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All	Dimensi	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type E)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	1.650		
X3	1.650		
X4	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com